2SC4900

Silicon NPN Epitaxial

HITACHI

Application

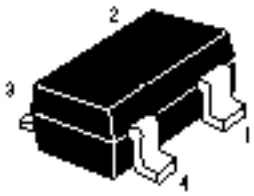
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 9 GHz Typ
- High gain, low noise figure
  PG = 13.0 dB Typ, NF = 1.2 dB Typ at f = 900 MHz

Outline

MPAK-4



1. Collector
2. Emitter
3. Base
4. Emitter

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

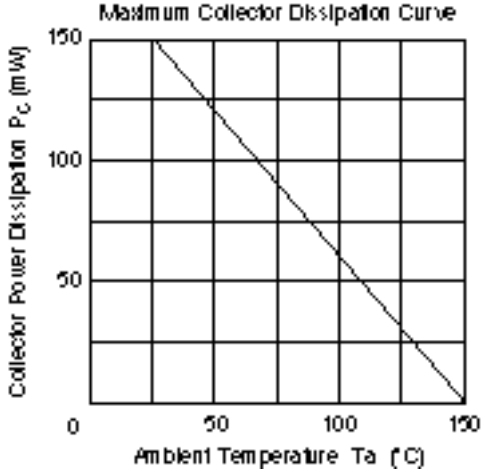
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	9	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

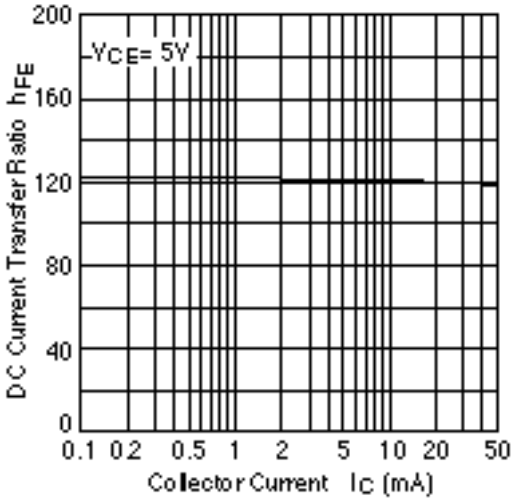
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	I_C = 10 µA, I_E = 0
Collector cutoff current	I_{CBO}	—	—	10	µA	V_{CB} = 12 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 9 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 1.5 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 5 V, I_C = 20 mA
Collector output capacitance	Cob	—	0.8	1.3	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	6.0	9.0	—	GHz	V_{CE} = 5 V, I_C = 20 mA
Power gain	PG	10.5	13.5	—	dB	V_{CE} = 5 V, I_C = 20 mA, f = 900 MHz
Noise figure	NF	—	1.2	2.5	dB	V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz

Note: Marking is “YJ–”.

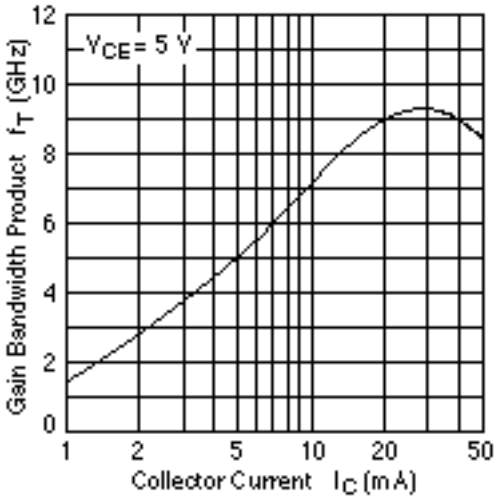
Maximum Collector Dissipation Curve



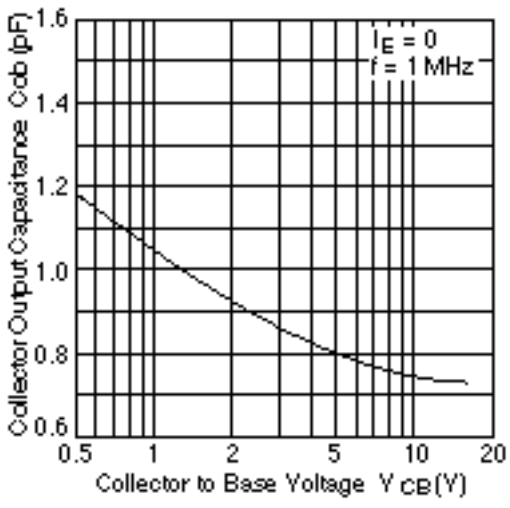
DC Current Transfer Ratio vs. Collector Current



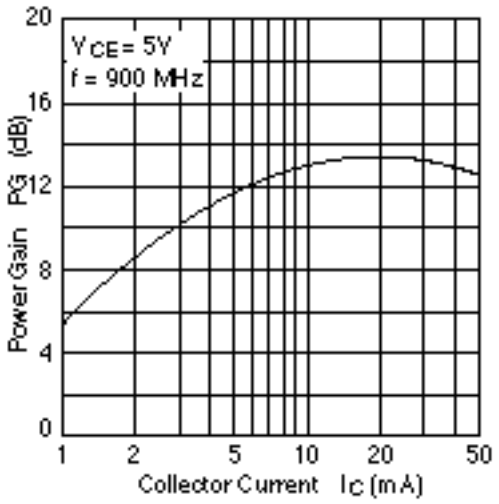
Gain Bandwidth Product vs. Collector Current



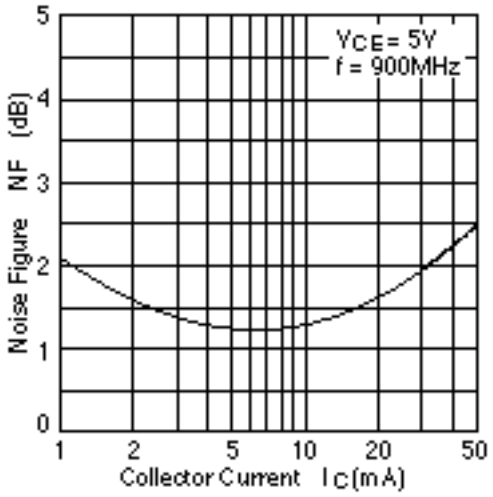
Collector Output Capacitance vs. Collector to Base Voltage



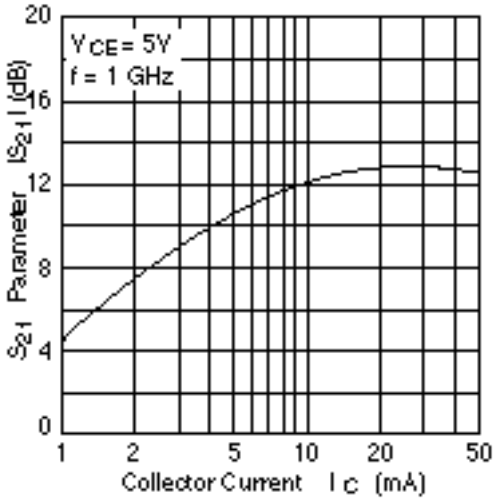
Power Gain vs. Collector Current



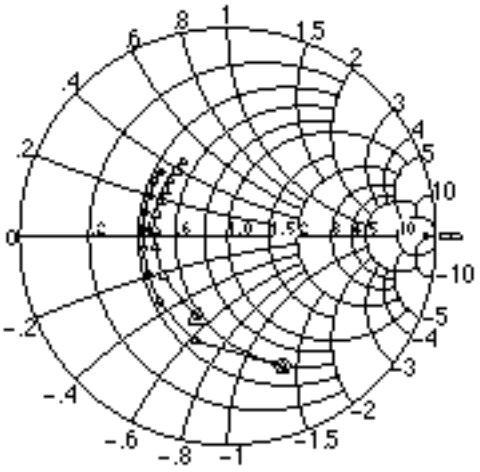
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

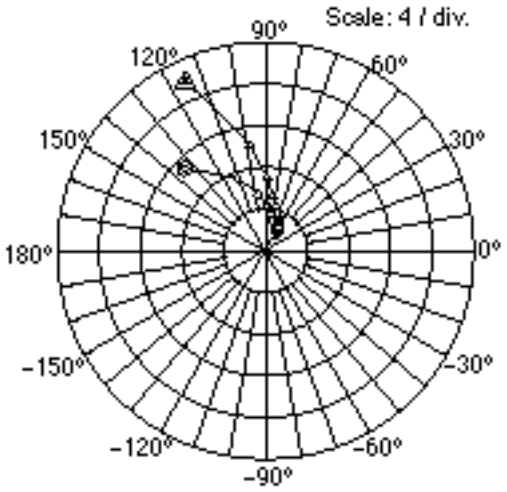


S11 Parameter vs. Frequency



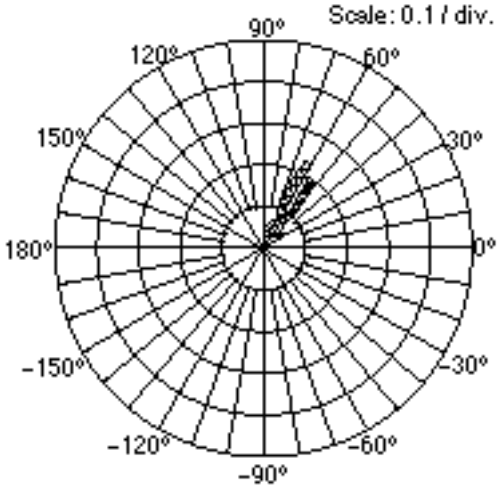
Condition: V_{CE} = 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S21 Parameter vs. Frequency



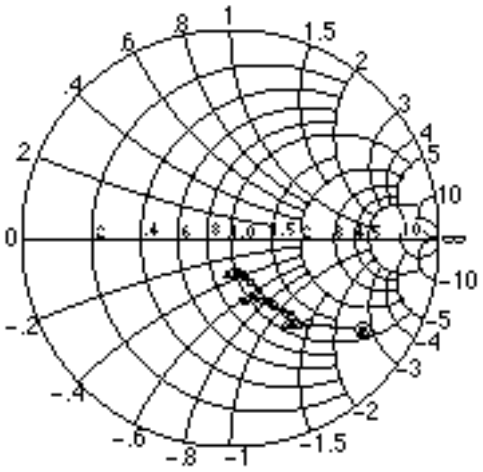
Condition: V_{CE} = 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S Parameter (V_{CE} = 5 V, I_C = 5 mA, Z_O = 50 Ω, Emitter Common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.678	–67.0	11.09	134.6	0.0572	59.2	0.772	–34.7
400	0.523	–107.6	7.49	111.6	0.0802	48.8	0.556	–47.8
600	0.453	–135.8	5.43	98.3	0.0933	47.1	0.443	–53.7
800	0.423	–155.2	4.24	89.0	0.105	47.8	0.382	–57.2
1000	0.407	–172.1	3.47	81.6	0.118	49.7	0.348	–60.2
1200	0.412	174.7	2.94	75.0	0.130	50.7	0.330	–62.9
1400	0.414	163.5	2.54	69.2	0.145	51.9	0.318	–66.5
1600	0.423	152.3	2.26	64.3	0.158	52.7	0.312	–70.3
1800	0.438	143.2	2.05	59.2	0.174	53.3	0.307	–74.4
2000	0.446	135.7	1.87	55.0	0.189	53.4	0.305	–78.4

S Parameter (V_{CE} = 5 V, I_C = 20 mA, Z_O = 50 Ω, Emitter Common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.420	–110.3	17.91	115.5	0.0381	59.7	0.502	–54.1
400	0.362	–148.9	10.13	98.4	0.0572	62.2	0.311	–62.8
600	0.351	–170.5	6.94	89.2	0.0766	64.7	0.240	–66.1
800	0.352	175.2	5.29	82.9	0.0966	65.7	0.207	–69.1
1000	0.361	162.7	4.27	77.1	0.117	65.8	0.189	–71.6
1200	0.364	153.1	3.60	72.3	0.138	65.1	0.181	–75.1
1400	0.373	143.9	3.12	67.9	0.158	64.0	0.178	–79.3
1600	0.386	136.2	2.76	63.6	0.178	62.5	0.176	–83.3
1800	0.396	128.2	2.49	59.4	0.199	61.3	0.177	–87.5
2000	0.414	121.3	2.27	55.5	0.218	59.8	0.178	–91.9

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